

## TPS65235-1 LNB 稳压器，具有 I<sup>2</sup>C 接口

### 1 特性

- 用于 LNB 和 I<sup>2</sup>C 接口的完整集成解决方案
- 兼容 DiSEqC 2.x 和 DiSEqC 1.x
- 支持 5V、12V 和 15V 电源轨
- 高达 1000mA 的外部电阻器可调精确输出电流限制
- 升压开关峰值电流限制，与 LDO 电流限制成正比
- 具有 140mΩ 低 R<sub>ds(on)</sub> 内部电源开关的升压转换器
- 可选择 1MHz 或 500kHz 升压开关频率
- 在强制 PWM 模式下能避免可闻噪声
- 适用于非 I<sup>2</sup>C 应用的专用使能引脚
- 具有推挽式输出级的低压降 (LDO) 稳压器，用于提供 VLNB 输出
- 内置精确的 22kHz 音调发生器并支持外部音调输入
- 支持 44kHz 和 22kHz 外部音调输入
- 可调节软启动和 13V 至 18V 电压转换时间
- 650mV 至 750mV 的 22kHz 音调振幅选择
- 通过在 EN 为低电平时进行访问的 I<sup>2</sup>C 寄存器
- 短路动态保护
- 输出电压电平、DiSEqC 音调输入和输出、电流电平以及电缆连接诊断
- 具有过热保护功能
- 20 引脚 WQFN 3mm x 3mm (RUK) 封装

### 2 应用

- [机顶盒卫星接收器](#)
- [电视卫星接收器](#)
- [PC 卡卫星接收器](#)
- [卫星电视](#)

### 3 说明

TPS65235-1 专为模拟和数字卫星接收器而设计，是一款具有 I<sup>2</sup>C 接口的单片稳压器。该器件专用于向碟形天线中的 LNB 降压转换器或多开关箱提供 13V 至 18V 电源以及 22kHz 音调信号。该器件将极少的组件数、低功率耗散、简单设计与 I<sup>2</sup>C 标准接口相结合，能够提供一套完整的解决方案。

TPS65235-1 具有高效能。该升压转换器集成了一个在 1MHz 或 500kHz 可选开关频率下运行的 140mΩ 功率 MOSFET。线性稳压器中的压降为 0.8V，能够更大幅度地降低功率损耗。TPS65235-1 提供多种方式来生成 22kHz 信号。具有推挽式输出级的集成线性稳压器可生成 22kHz 音调信号（在输出端叠加），即使在零负载条件下也是如此。可由外部电阻器以 ±10% 的精度来设定线性稳压器的电流限值。通过 I<sup>2</sup>C 读取的全范围诊断可用于系统监控。

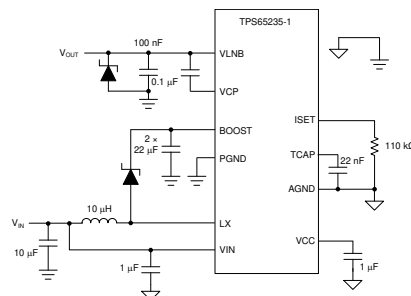
TPS65235-1 在 FCCM 模式下具有特殊设计，以避免可闻噪声，尤其是当 VIN 高于或接近 VLNB 输出时。

TPS65235-1 支持面向 22kHz 音调检测电路和输出接口的高级 DiSEqC 2.x 标准。

#### 器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
TPS65235-1	WQFN	3.00mm × 3.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



简化版原理图



## Table of Contents

1 特性.....	1	7.6 Register Maps.....	21
2 应用.....	1	<b>8 Application and Implementation.....</b>	<b>24</b>
3 说明.....	1	8.1 Application Information.....	24
4 Revision History.....	2	8.2 Typical Application.....	24
5 Pin Configuration and Functions.....	3	<b>9 Power Supply Recommendations.....</b>	<b>30</b>
6 Specifications.....	4	<b>10 Layout.....</b>	<b>31</b>
6.1 Absolute Maximum Ratings.....	4	10.1 Layout Guidelines.....	31
6.2 ESD Ratings.....	4	10.2 Layout Example.....	32
6.3 Recommended Operating Conditions.....	4	<b>11 Device and Documentation Support.....</b>	<b>33</b>
6.4 Thermal Information.....	4	11.1 Device Support.....	33
6.5 Electrical Characteristics.....	5	11.2 Documentation Support.....	33
6.6 Timing Requirements.....	7	11.3 接收文档更新通知.....	33
6.7 Typical Characteristics.....	8	11.4 支持资源.....	33
<b>7 Detailed Description.....</b>	<b>9</b>	11.5 Trademarks.....	33
7.1 Overview.....	9	11.6 Electrostatic Discharge Caution.....	33
7.2 Functional Block Diagram.....	9	11.7 术语表.....	33
7.3 Feature Description.....	9	<b>12 Mechanical, Packaging, and Orderable Information.....</b>	<b>34</b>
7.4 Device Functional Modes.....	18		
7.5 Programming.....	19		

## 4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision D (July 2019) to Revision E (May 2021)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式。.....	1
• Changed $V_{(drop)}$ min and max values.....	5
• Changed $I_{(rev\_dis)}$ min and max values.....	5
Changes from Revision C (July 2018) to Revision D (July 2019)	Page
• Changed $V_{(drop)}$ at TONEAMP = 0b From: MIN = 0.44 TYP = 0.7 MAX = 1 To: MIN = 0.49 TYP = 0.8 MAX = 1.1 in the <i>Electrical Characteristics</i> .....	5
• Changed $V_{(drop)}$ at TONEAMP = 1b From: MIN = 0.55 TYP = 0.8 MAX = 1.12 To: MIN = 0.65 TYP = 0.9 MAX = 1.2 in the <i>Electrical Characteristics</i> .....	5
Changes from Revision B (June 2018) to Revision C (July 2018)	Page
• Changed the GDR TONE_TRANS = 1b value From: MAX = 24.03V To: MAX = 24.33V in the <i>Electrical Characteristics</i> .....	5
Changes from Revision A (January 2017) to Revision B (December 2017)	Page
• Changed bit 4 (T125) in 表 7-8 From: 0b = Die temperature > 125°C To: 0b = Die temperature > 125°C and From: 1b = Die temperature < 125°C To: 1b = Die temperature > 125°C.....	23
Changes from Revision * (January 2017) to Revision A (December 2017)	Page
• Changed the VCP values From: VLNB to 7 V To: - 0.3 V to 7 V in the <i>Absolute Maximum Ratings</i> .....	4
• Changed the GDR values From: VLNB to VCP To: - 0.3 V to 7 V in the <i>Absolute Maximum Ratings</i> .....	4
• Changed the $A_{(tone)}$ TONEAMP = 0b values From: MIN = 667 TYP = 700 MAX = 746 To: MIN = 617 TYP = 650 MAX = 696 in the <i>Electrical Characteristics</i> .....	5
• Changed the $A_{(tone)}$ TONEAMP = 1b values From: MIN = 753 TYP = 800 MAX = 853 To: MIN = 703 TYP = 750 MAX = 803 in the <i>Electrical Characteristics</i> .....	5

## 5 Pin Configuration and Functions

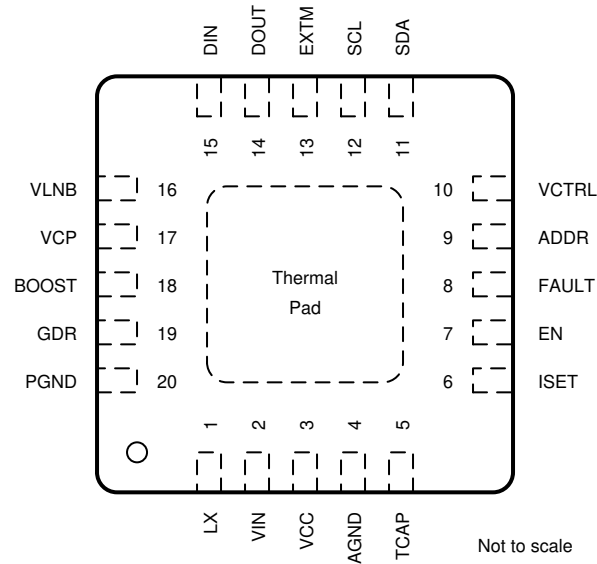


图 5-1. RUK Package 20-Pin WQFN With Exposed Thermal Pad Top View

表 5-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NO.	NAME		
1	LX	I	Switching node of the boost converter
2	VIN	S	Input of internal linear regulator
3	VCC	O	Internal 6.3-V power supply. Connect a 1- $\mu$ F ceramic capacitor from this pin to ground. When $V_{IN}$ is 5 V, connect the VCC pin to the VIN pin.
4	AGND	S	Analog ground. Connect all ground pins and power pad together.
5	TCAP	O	Connect a capacitor to this pin to set the rise time of the LNB output.
6	ISET	O	Connect a resistor to this pin to set the LNB output current limit.
7	EN	I	Enable this pin to enable the VLNB output. pull this pin to ground to disable the output. The output is then pulled to ground, and, when the EN pin is low, the I <sup>2</sup> C interface can be accessed.
8	FAULT	O	Open drain output pin, it goes low if any fault flag is set.
9	ADDR	I	Connect a different resistor to this pin to set different I <sup>2</sup> C addresses (see the 表 7-4 table).
10	VCTRL	I	Voltage level at this pin to set the output voltage (see the 表 7-3).
11	SDA	I/O	I <sup>2</sup> C compatible bidirectional data
12	SCL	I	I <sup>2</sup> C compatible clock input
13	EXTM	I	External modulation logic input pin that activates the 22-kHz tone output. The feeding signal can be 22-kHz tone or logic high or low.
14	DOUT	O	Tone detection output
15	DIN	I	Tone detection input
16	VLNB	O	Output of the power supply connected to satellite receiver or switch
17	VCP	O	Gate drive supply voltage and output of charge pump. Connect a capacitor between this pin and the VLNB pin.
18	BOOST	O	Output of the boost regulator and Input voltage of the internal linear regulator
19	GDR	O	Control the gate of the external MOSFET for DiSEqc 2.x support
20	PGND	S	Power ground for the boost converter
—	Thermal Pad	—	The thermal pad must be soldered to the printed circuit board (PCB) for optimal thermal performance. Use thermal vias on the PCB to enhance power dissipation.

(1) I = input, O = output, I/O = input and output, S = power supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	VIN, LX, BOOST, VLNB	1	30	V
	VCP, GDR (referenced to VLNB pin)	- 0.3	7	
	VCC, EN, ADDR, FAULT, SCL, SDA, VCTRL, EXTM, DOUT, DIN, TCAP	- 0.3	7	
	ISET	- 0.3	3.6	
	PGND	- 0.3	0.3	
Operating junction temperature, T <sub>J</sub>		- 40	150	°C
Storage temperature, T <sub>stg</sub>		- 55	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±4000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.  
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>IN</sub>	Input operating voltage	4.5		20	V
T <sub>A</sub>	Operating junction temperature	- 40		125	°C

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS65235-1	UNIT
		RUK (WQFN)	
		20 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	44.8	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	47.3	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	16.5	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	0.5	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	16.4	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	3.6	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

## 6.5 Electrical Characteristics

-40°C ≤ T<sub>J</sub> ≤ 125°C, V<sub>IN</sub> = 12 V, f<sub>SW</sub> = 1 MHz (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>INPUT SUPPLY</b>						
V <sub>IN</sub>	Input voltage range		4.5	12	20	V
I <sub>DD(SDN)</sub>	Shutdown supply current	EN = 0b	90	120	150	μA
I <sub>LDO(Q)</sub>	LDO quiescent current	EN = 1b, I <sub>O</sub> = 0 A, V <sub>VLNB</sub> = 18.2 V	1.5	5	8.5	mA
UVLO	V <sub>IN</sub> undervoltage lockout	V <sub>IN</sub> rising	4.15	4.3	4.45	V
		Hysteresis	280	480	550	mV
<b>OUTPUT VOLTAGE</b>						
V <sub>OUT</sub>	Regulated output voltage	V <sub>(ctrl)</sub> = 1, I <sub>O</sub> = 500 mA	18	18.2	18.4	V
		V <sub>(ctrl)</sub> = 0, I <sub>O</sub> = 500 mA	13.25	13.4	13.55	V
		SCL = 1b, V <sub>(ctrl)</sub> = 1, I <sub>O</sub> = 500 mA (Non I <sup>2</sup> C)	19.18	19.4	19.62	V
		SCL = 1b, V <sub>(ctrl)</sub> = 0, I <sub>O</sub> = 500 mA (Non I <sup>2</sup> C)	14.44	14.6	14.76	V
I <sub>(OCP)</sub>	Output short circuit current limit	R <sub>(SET)</sub> = 200 kΩ, Full temperature	580	650	720	mA
		T <sub>J</sub> = 25°C	629	650	688	mA
f <sub>SW</sub>	Boost switching frequency	f = 1 MHz	977	1060	1134	kHz
I <sub>(limitsw)</sub> <sup>(1)</sup>	Switching current limit	V <sub>IN</sub> = 12 V, V <sub>OUT</sub> = 18.2 V, R <sub>(SET)</sub> = 200 kΩ		3		A
R <sub>ds(on)_LS</sub>	On resistance of low side FET	V <sub>IN</sub> = 12 V	90	140	210	mΩ
V <sub>(drop)</sub>	Linear regulator voltage dropout	I <sub>O</sub> = 500 mA, TONEAMP = 0b	0.44	0.8	1.15	V
		I <sub>O</sub> = 500 mA, TONEAMP = 1b	0.55	0.9	1.2	V
I <sub>(cable)</sub>	Cable good detection current threshold	V <sub>IN</sub> = 12 V, V <sub>OUT</sub> = 13.4 V or 18.2 V	0.9	5	8.8	mA
I <sub>(rev)</sub>	Reverse bias current	EN = 1b, V <sub>VLNB</sub> = 21 V	49	58	65	mA
I <sub>(rev_dis)</sub>	Disabled reverse bias current	EN = 0b, V <sub>VLNB</sub> = 21 V	2.9	4.6	6.3	mA
<b>LOGIC SIGNALS</b>						
	Enable threshold (V <sub>(EN)</sub> ), high		1.6			V
	Enable threshold (V <sub>(EN)</sub> ), low				0.8	V
I <sub>(EN)</sub>	Enable internal pullup current	V <sub>(EN)</sub> = 1.5 V	5	6	7	μA
		V <sub>(EN)</sub> = 1 V	2	3	4	μA
V <sub>(VCTRL_H)</sub>	VCTRL logic threshold level for high-level input voltage		2			V
V <sub>(VCTRL_L)</sub>	VCTRL logic threshold level for low-level input voltage				0.8	V
V <sub>(EXTM_H)</sub>	EXTM logic threshold level for high-level input voltage		2			V
V <sub>(EXTM_L)</sub>	EXTM logic threshold level for low-level input voltage				0.8	V
V <sub>OL(FAULT)</sub>	FAULT output low voltage	FAULT open drain, I <sub>OL</sub> = 1 mA			0.4	V
<b>-tone</b>						
f <sub>(tone)</sub>	Tone frequency	22-kHz tone output	20	22	24	kHz
A <sub>(tone)</sub>	Tone amplitude	0 mA ≤ I <sub>O</sub> ≤ 500 mA, C <sub>O</sub> = 100 nF, TONEAMP = 0b	617	650	696	mV
		0 mA ≤ I <sub>O</sub> ≤ 500 mA, C <sub>O</sub> = 100 nF, TONEAMP = 1b	703	750	803	mV
D <sub>(tone)</sub>	Tone duty cycle		45%	50%	55%	
f <sub>(EXTM)</sub>	External tone input frequency range	22-kHz tone output	17.6	22	26.4	kHz
		44-kHz tone output	35.2	44	52.8	kHz

**TPS65235-1**

ZHCSG04E - JANUARY 2017 - REVISED MAY 2021

 $-40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C}$ ,  $V_{IN} = 12\text{ V}$ ,  $f_{SW} = 1\text{ MHz}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>-tone DETECTION</b>						
$f_{(DIN)}$	Tone detector frequency capture range	0.4- $V_{PP}$ sine wave	17.6	22	26.4	kHz
$V_{(DIN)}$	Tone detector input amplitude	Sine wave, 22 kHz	0.3		1.5	V
$V_{(DOUT)}$	DOUT output voltage	Tone present, $I_{load} = 2\text{ mA}$			0.4	V
GDR	Bypass FET gate voltage, LNB	TONE_TRANS = 1b, $V_{(LNB)} = 18.2\text{ V}$	23.11	23.5	24.33	V
		TONE_TRANS = 0b, $V_{(LNB)} = 18.2\text{ V}$	18.17	18.2	18.23	V
<b>Thermal SHUT-DOWN (JUNCTION TEMPERATURE)</b>						
$T_{(TRIP)}$	Thermal protection trip point	Temperature rising		160		$^{\circ}\text{C}$
$T_{(HYST)}$	Thermal protection hysteresis			20		$^{\circ}\text{C}$
<b>I<sup>2</sup>C READ BACK FAULT STATUS</b>						
$V_{(PGOOD)}$	PGOOD trip levels	Feedback voltage UVP low	94%	96%	97.1%	
		Feedback voltage UVP high	93%	94.5%	95.5%	
		Feedback voltage OVP high	104%	106.6%	108%	
		Feedback voltage OVP low	102%	104.6%	106%	
$T_{(warn)}$	Temperature warning threshold		125			$^{\circ}\text{C}$
<b>I<sup>2</sup>C INTERFACE</b>						
$V_{IH}$	SDA,SCL input high voltage		2			V
$V_{IL}$	SDA,SCL input low voltage				0.8	V
$I_I$	Input current	SDA, SCL, $0.4\text{ V} \leq V_I \leq 4.5\text{ V}$	- 10		10	$\mu\text{A}$
$V_{OL}$	SDA output low voltage	SDA open drain, $I_{OL} = 2\text{ mA}$			0.4	V
$f_{(SCL)}$	Maximum SCL clock frequency		400			kHz

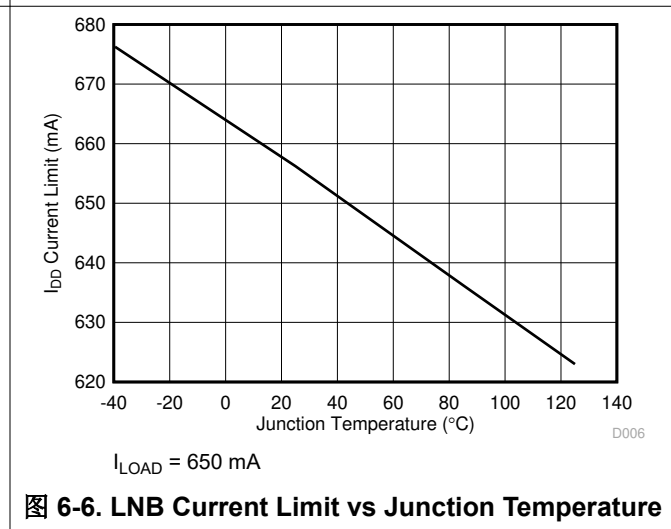
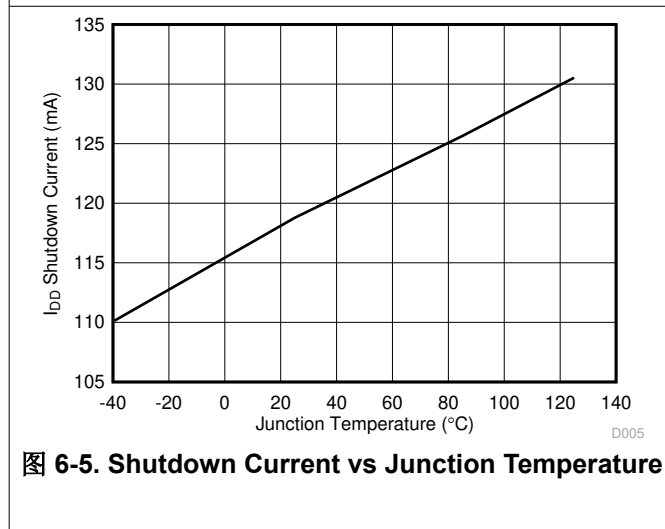
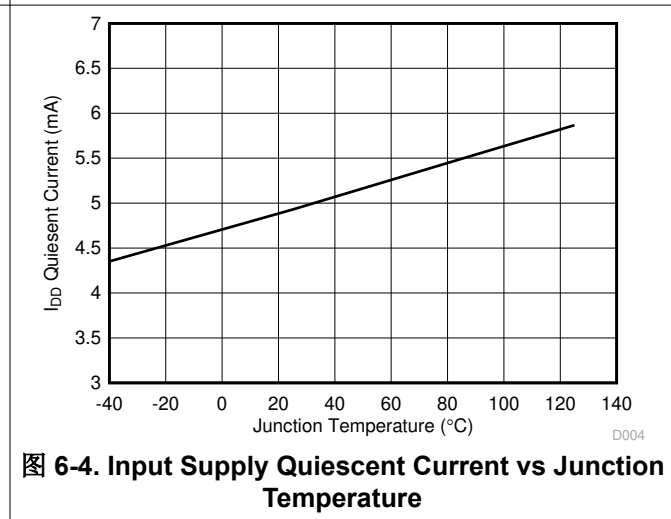
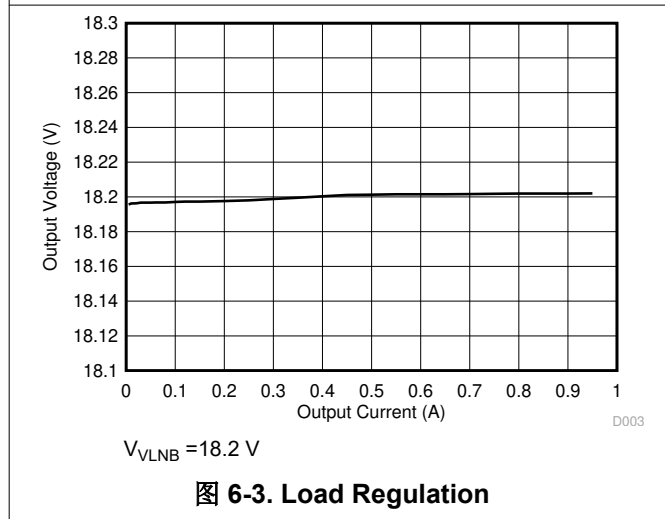
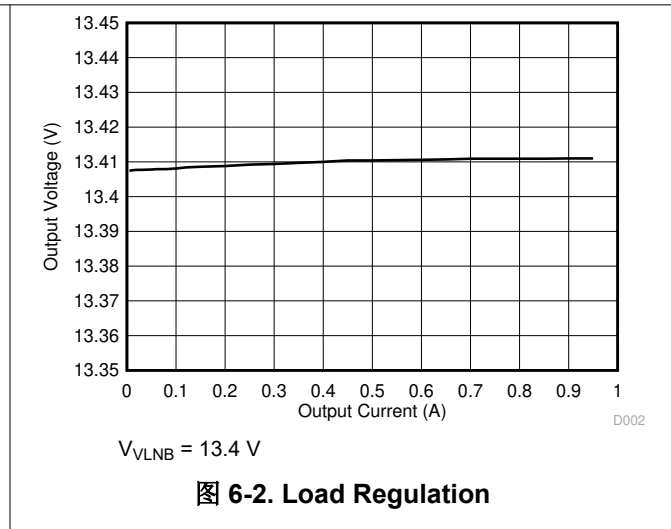
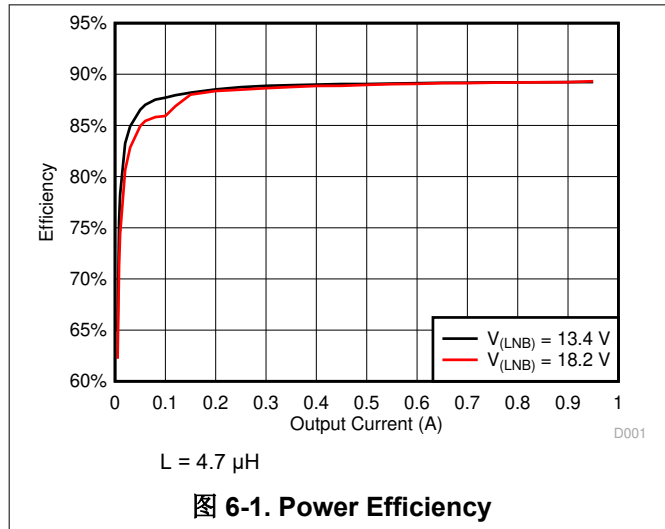
(1) Specified by design

## 6.6 Timing Requirements

			MIN	NOM	MAX	UNIT
<b>OUTPUT VOLTAGE</b>						
$t_r, t_f$	13-V to 18-V transition rising falling time	$C_{(TCAP)} = 22 \text{ nF}$	2			ms
$t_{ON(min)}$	Minimum on time for the Low side FET		75	102	130	ns
<b>TONE</b>						
$t_{r(tone)}$	Tone rise time	$0 \text{ mA} \leq I_O \leq 500 \text{ mA}, C_O = 100 \text{ nF},$ Control Reg1[0] = 0b	11			$\mu\text{s}$
		$0 \text{ mA} \leq I_O \leq 500 \text{ mA}, C_O = 100 \text{ nF},$ Control Reg1[0] = 1b, and EXTM has 44-kHz input	5.5			$\mu\text{s}$
$t_{f(tone)}$	Tone fall time	$0 \text{ mA} \leq I_O \leq 500 \text{ mA}, C_O = 100 \text{ nF},$ Control Reg1[0] = 0b	10.8			$\mu\text{s}$
		$0 \text{ mA} \leq I_O \leq 500 \text{ mA}, C_O = 100 \text{ nF},$ Control Reg1[0] = 1b, and EXTM has 44 kHz input	5.4			$\mu\text{s}$
<b>OVERCURRENT PROTECTION</b>						
$t_{ON}$	Overcurrent protection ON time	TIMER = 0b	2.3	3.75	5.52	ms
$t_{OFF}$	Overcurrent protection OFF time	TIMER = 0b	98.5	118	133.5	ms
<b>I<sup>2</sup>C INTERFACE</b>						
$t_{BUF}$	Bus free time between a STOP and START condition		1.3			$\mu\text{s}$
$t_{HD\_STA}$	Hold time (repeated) START condition		0.6			$\mu\text{s}$
$t_{SU\_STO}$	Setup time for STOP condition		0.6			$\mu\text{s}$
$t_{LOW}$	LOW period of the SCL clock		1			$\mu\text{s}$
$t_{HIGH}$	HIGH period of the SCL clock		0.6			$\mu\text{s}$
$t_{SU\_STA}$	Setup time for a repeated START condition		0.6			$\mu\text{s}$
$t_{SU\_DAT}$	Data setup time		0.1			$\mu\text{s}$
$t_{HD\_DAT}$	Data hold time		0			0.9 $\mu\text{s}$
$t_{RCL}$	Rise time of SCL signal	Capacitance of one bus line (pF)	$20 + 0.1 C_B$			300 ns
$t_{RCL1}$	Rise time of SCL Signal after a Repeated START condition and after an acknowledge BIT	Capacitance of one bus line (pF)	$20 + 0.1 C_B$			300 ns
$t_{FCL}$	Fall time of SCL signal	Capacitance of one bus line (pF)	$20 + 0.1 C_B$			300 ns
$t_{RDA}$	Rise time of SDA signal	Capacitance of one bus line (pF)	$20 + 0.1 C_B$			300 ns
$t_{FDA}$	Fall time of SDA signal	Capacitance of one bus line (pF)	$20 + 0.1 C_B$			300 ns
$C_B$	Capacitance of one bus line(SCL and SDA)					400 pF

## 6.7 Typical Characteristics

$T_A = 25^\circ\text{C}$ ,  $V_{IN} = 12\text{ V}$ ,  $f_{SW} = 1\text{ MHz}$ ,  $C_{Boost} = (2 \times 22\ \mu\text{F} / 35\text{ V})$  (unless otherwise noted)





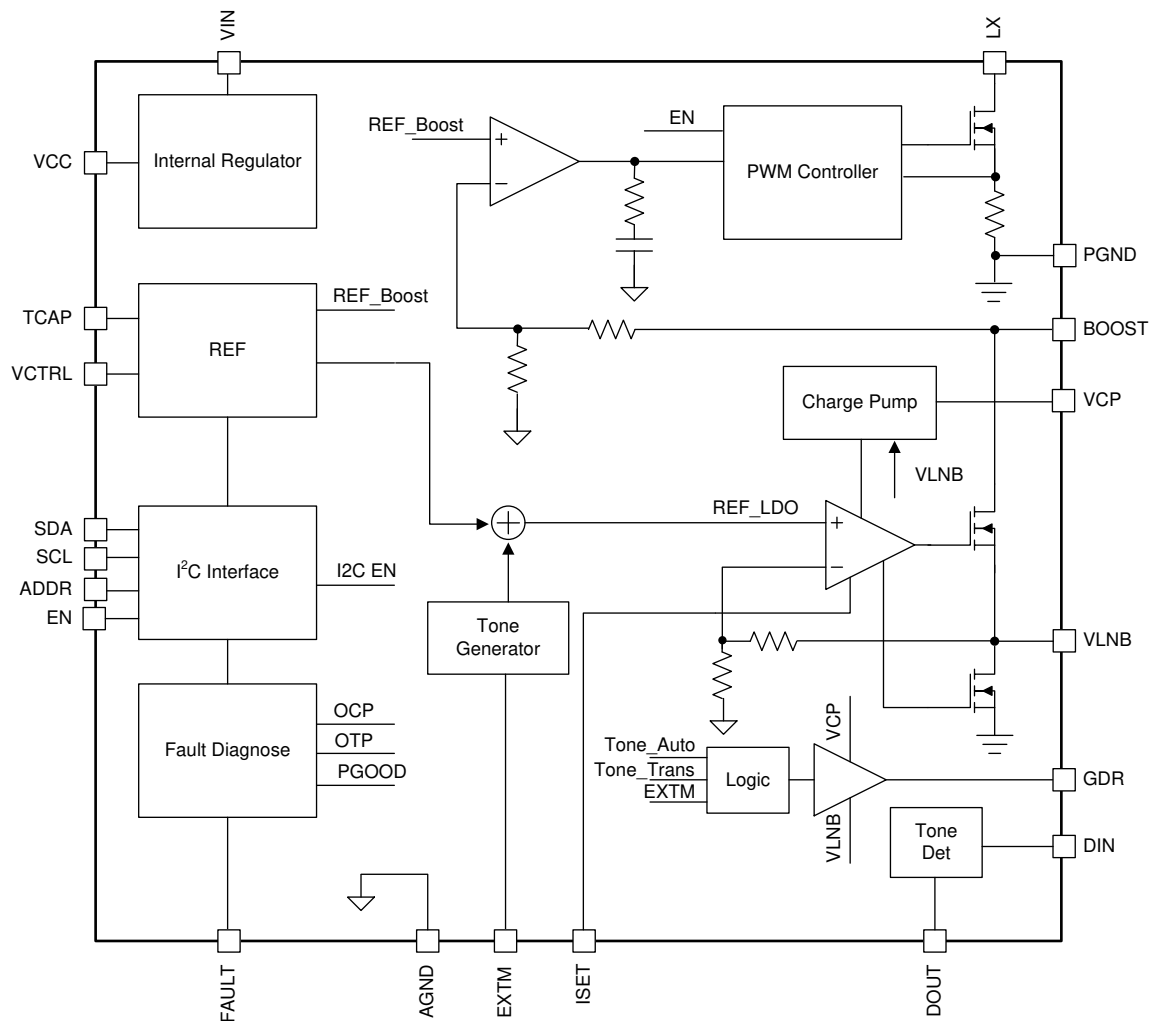
## 7 Detailed Description

### 7.1 Overview

The TPS65235-1 device is the power management IC (PMIC) that integrates a boost converter, an LDO regulator, and a 22-kHz tone generator to serve as a LNB power supply. This solution compiles the DiSEqC 2.x standard with or without I<sup>2</sup>C interface. An external resistor allows for precise programming of the output current limit. The 22-kHz tone signal can be generated in one of two ways, either with or without I<sup>2</sup>C. The integrated boost features low R<sub>ds(on)</sub> MOSFET and internal compensation. A selectable switching frequency of 1 MHz or 500 kHz is designed to reduce the size of passive components and be flexible for design.

The TPS65235-1 device can support the 44-kHz tone output. When the EXTM pin has a 44-kHz tone input, and the EXTM TONE bit in the [Control Register 1](#) is set to 1b, the LNB tone output is 44 kHz. By default, the TPS65235-1 device has a typical 22-kHz tone output.

### 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 Boost Converter

The TPS65235-1 device has an internal compensated boost converter and low-dropout (LDO) linear regulator. The boost converter tracks the LNB output voltage within 800 mV even at loading 1000 mA, which minimizes power loss.

The boost converter operates at 1 MHz by default. The TPS65235-1 device has internal cycle-by-cycle peak current limit in the boost converter and DC current limit in the LNB output to help protect the device from short

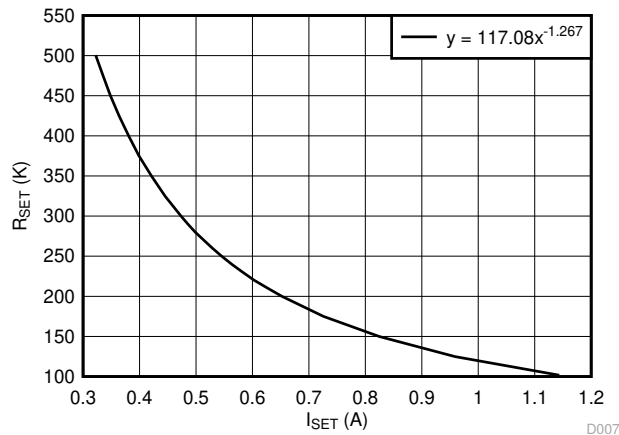
circuits and over loading. When the LNB output is shorted to ground, the LNB output current is clamped at the LDO current limit. The LDO current limit is set by the external resistor at the ISET pin. The current limit of the boost switch is proportional to the LDO current limit. If an overcurrent condition occurs for more than 4 ms, the boost converter enters hiccup mode and retries startup in 128 ms. This hiccup mode ON time and OFF time are selectable through the I<sup>2</sup>C control register (address 0x01) to be either 4 ms and 128 ms or 8 ms and 256 ms, respectively. At extremely light loads, the boost converter automatically operates in a pulse-skipping mode.

The boost converter is stable with either ceramic capacitor or electrolytic capacitor.

If two or more set-top box LNB outputs are connected together, one output voltage can be set higher than others. The output with the lower set voltage is then effectively turned off. When the voltage drops to the set level, the LNB output with the lower set output voltage returns to normal conditions.

### 7.3.2 Linear Regulator and Current Limit

The linear regulator is used to generate the 22-kHz tone signal by changing the LDO reference voltage. The linear regulator features low-dropout voltage to minimize power loss while maintaining enough head room for the 22-kHz tone with 650-mV amplitude. The linear regulator also implements a tight current limit for overcurrent protection. The current limit is set by an external resistor connected to ISET pin. [图 7-1](#) shows the relationship between the current limit threshold and the resistor value.



**图 7-1. Linear Regulator Current Limit Vs Resistor**

$$R_{SET}(k\Omega) = 117.08 \times I_{SET}^{-1.267}(A) \quad (1)$$

A 200-k $\Omega$  resistor sets the current to 0.65 A, and 110-k $\Omega$  resistor sets the current to approximately 1 A.

### 7.3.3 Boost Converter Current Limit

The boost converter has the cycle-by-cycle peak current limit on the internal Power MOSFET switch to serve as the secondary protection when LNB output is hard short. With ISW bit default setting 0b on I<sup>2</sup>C control register 0x01, the switch current limit I<sub>SW</sub> is proportional as LDO current limit I<sub>(OCP)</sub> set by ISET pin resistor, and the relationship can be expressed as:

$$I_{SW} = 3 \times I_{(OCP)} + 0.8A \quad (2)$$

For the 5 V V<sub>IN</sub>, if LNB current load is up to 1 A, the ISW bit should be written as 1b, the switch current limit I<sub>SW</sub> for the internal Power MOSFET is:

$$I_{SW} = 5 \times I_{(OCP)} + 0.8A \quad (3)$$

While due to the high power loss at 5 V, V<sub>IN</sub>, it has a chance to trigger the thermal shutdown before the loading is up to 1 A, especially the VLNB output is high.

### 7.3.4 Charge Pump

The charge pump circuitry generates a voltage to drive the NMOS of the linear regulator. The voltage across the charge pump capacitor between VLNB and VCP is about 5.4 V, so the absolute value of the VCP voltage will be VLNB + 5.4 V.

### 7.3.5 Slew Rate Control

When LNB output voltage transits from 13.4 V to 18.2 V or 18.2 V to 13.4 V, the cap at pin TCAP controls the transition time. This transition time makes sure the boost converter output to follow LNB output change. Usually boost converter has low bandwidth and can't response fast. The voltage at TCAP acts as the reference voltage of the linear regulator. The boost converter's reference is also based on TCAP with additional fixed voltage to generate a 0.8 V above the LNB output.

The charging and discharging current is 10 μA, thus the transition time can be estimated as:

$$t_{TCAP}(ms) = 0.8 \times \frac{C_{SS}(nF)}{I_{SS}(\mu A)} \quad (4)$$

A 22-nF capacitor generates about 2 ms transition time.

In light load conditions, when LNB output voltage is set from 18.2 V to 13.4 V, the voltage drops very slow, which causes wrong VOUT\_GOOD (Bit 0 at status register 0x02) logic for LNB output voltage detection. TPS65235-1 has integrated a pull down circuit to pull down the output during the transition. This ensures the voltage change can follow the voltage at TCAP. When the 22-kHz tone signal is superimposing on the LNB output voltage, the pull down current can also provide square wave instead of a distorted waveforms.

### 7.3.6 Short Circuit Protection, Hiccup and Overtemperature Protection

The LNB output current limit can be set by an external resistor. When short circuit conditions occur or current limit is triggered, the output current is clamped at the current limit for 4 ms with LDO on. If the condition retains, the converter will shut down for 128 ms and then restart. This hiccup behavior prevents IC from being overheat. The hiccup ON/OFF time can be set by I<sup>2</sup>C register. Refer to [Control Register 1](#) for detail.

The low side MOSFET of the boost converter has a peak current limit threshold which serves as the secondary protection. If boost converter's peak current limit is triggered, the peak current will be clamped as high as 3.8 A when setting I<sub>SW</sub> default and LNB current limit up to 1 A. If loading current continues to increase, output voltage starts to drop and output power drops.

Thermal shutdown prevents the chip from operating at exceedingly high temperatures. When the junction temperature exceeds 160°C, the output shuts down. When the die temperature drops below its lower threshold typically 140°C, the output is enabled.

When the chip is in overcurrent protection or thermal shutdown, the I<sup>2</sup>C interface and logic are still active. The FAULT pin is pulled down to signal the processor. The FAULT pin signal remains low unless the following action is taken:

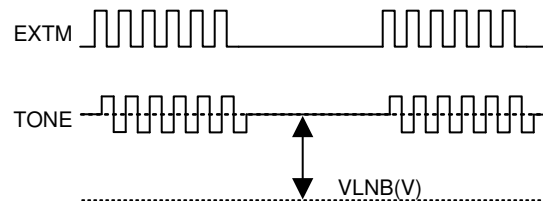
1. If I<sup>2</sup>C interface is not used to control, EN pin must be recycled to pull the FAULT pin back to high.
2. If I<sup>2</sup>C interface is used, the I<sup>2</sup>C master need to read the status [Control Register 2](#), then the FAULT pin will be back to high.

### 7.3.7 Tone Generation

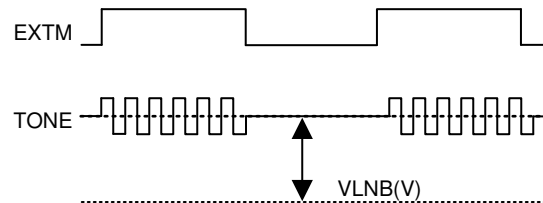
A 22-kHz tone signal is implemented at the LNB output voltage as a carrier for DiSEqC command. This tone signal can be generated by feeding an external 22-kHz clock at the EXTM pin, and it can also be generated with its internal tone generator controlled by EXTM pin. If EXTM pin is toggled to high, the internal tone signal will be superimposed at the LNB output, if EXTM pin is low, there will be no tone superimposed at the output stage of the regulator facilitates a push-pull circuit, so even at zero loading; the 22-kHz tone at the output is still clean without distortion.

There are two ways to generate the 22-kHz tone signal at the output.

For option1, if the EXTM has 44-kHz tone input, and the bit EXTM TONE of the [Control Register 1](#) is set to 1b, the LNB tone output is 44 kHz.



Option 1. Use external tone, gated by EXTM logic pulse



Option 2. Use internal tone, gated by EXTM logic envelop

**图 7-2. Two Ways to Generate 22-kHz tone**

### 7.3.8 Tone Detection

A 22-kHz tone detector is implemented in the TPS65235-1 solution. The detector extracts the AC-coupled tone signal from the DIN input and provides it as an open-drain signal on the DOUT pin. When the DOUTMODE bit in the [Control Register 2](#) is set to the default setting, if a tone is present, the DOUT output is logic low. If a tone is not present, the internal output FET is off. If a pullup resistor is connected to the DOUT pin, the output is logic high. The maximum tone out delay with respect to the input is one and a half of the tone cycle.

The DOUTMODE bit in the [Control Register 2](#) is reserved and should not be used.

### 7.3.9 Audio Noise Rejection

When the TPS65235-1 operates in PSM mode, locating the switching frequency at the range of audio frequency is possible. Which causes audible noise, especially when the VLNB voltage is lower or closer to the VIN voltage, and the current load is light.

When audible noise occurs, setting the TPS65235-1 device to operate in force PWM mode is recommended. In force PWM mode, a special design is implemented to avoid the audible noise.

### 7.3.10 Disable and Enable

The TPS65235-1 device has a dedicated EN pin to disable and enable the LNB output. In a non-I<sup>2</sup>C application, when the EN pin is pulled high, the LNB output is enabled. When the EN pin is pulled low, the LNB output is disabled. In an I<sup>2</sup>C application, when the EN pin is either low or high, the I<sup>2</sup>C registers can be accessed, which allows users to change the default LNB output at system power-up. When the I2C\_CON bit in the [Control Register 1](#) is set to 1b, the LNB output enable or disable is controlled by the EN bit in the [Control Register 2](#). By default, the I2C\_CON bit of the control register is set to 0b, which makes the LNB output is controlled by the EN pin. [图 7-3](#) and [图 7-4](#) shows the detailed control behavior.

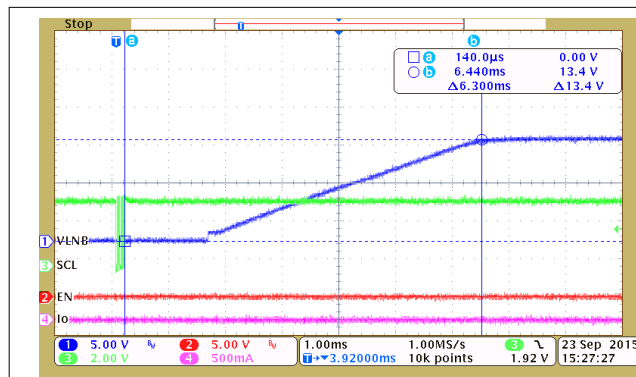


图 7-3. VLNB Output Controlled by bit EN of Control Register 2

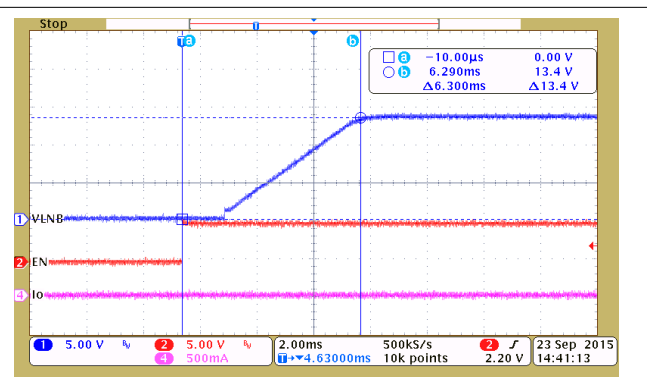


图 7-4. VLNB Output Controlled by EN Pin

### 7.3.11 Component Selection

#### 7.3.11.1 Boost Inductor

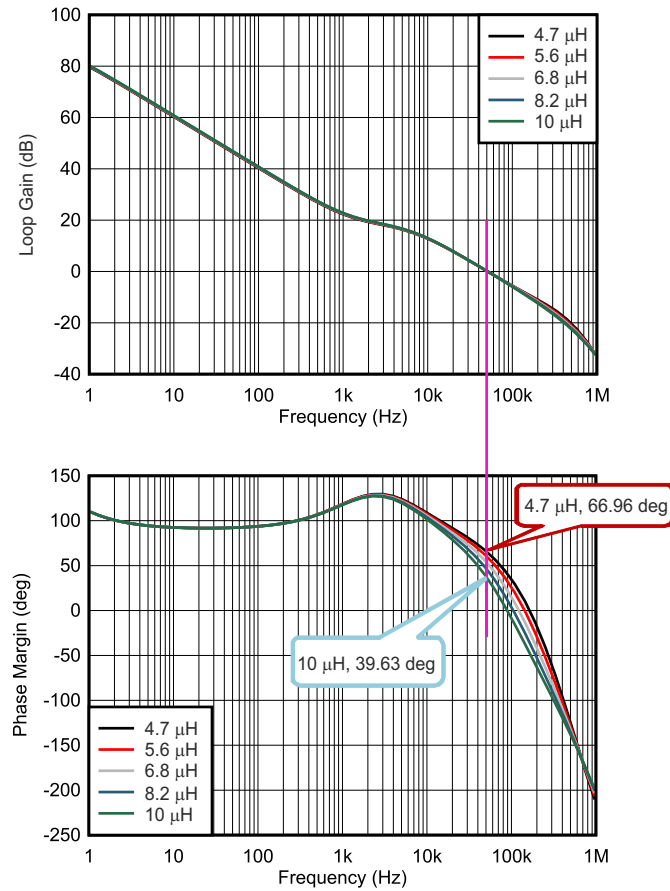
The TPS65235-1 device is recommended to operate with a boost inductor value of 4.7 μH or 10 μH. The boost inductor must be able to support the peak current requirement to maintain the maximum LNB output current without saturation. Use [方程式 5](#) to estimate the peak current of the boost inductor ( $I_{peak}$ ).

$$I_{peak} = \frac{I_{OUT}}{1-D} + \frac{1}{2} \times \frac{V_{IN} \times D}{L \times f_S} \quad (5)$$

where

$$D = 1 - \frac{V_{IN}}{V_{LNB} + 0.8} \quad (6)$$

With a different inductance, the system has different gain and phase margins. [图 7-5](#) shows a Bode plot of boost loop with 2 × 10 μF / 35 V of boost capacitor and 4.7 μH, 5.6 μH, 6.8 μH, 8.2 μH, and 10 μH of boost inductance. As the boost inductance increases, the 0-dB crossover frequency keeps relatively constant while reducing the phase and gain margins. With a 4.7-μH boost inductance, the phase margin is 66.96° and with a 10-μH inductance, the phase margin is 39.63°.



**图 7-5. Gain and Phase Margin of the Boost Loop with Different Inductance ( $V_{IN} = 12\text{ V}$ ,  $V_{OUT} = 18.2\text{ V}$ ,  $I_{LOAD} = 1\text{ A}$ ,  $f_{SW} = 1\text{ MHz}$ ,  $5\text{ }\mu\text{F}$ , Typical Bode Plot)**

**7.3.11.2 Capacitor Selection**

The TPS65235-1 device has a 1-MHz nonsynchronous boost converter integrated and the boost converter features the internal compensation network. The TPS65235-1 device works well with both ceramic capacitor and electrolytic capacitor.

The recommended ceramic capacitors for the TPS65235-1 application are, at the minimum, rated as X7R/X5R, with a 35-V rating, and a 1206 size for the achieving lower LNB output ripple. 表 7-1 lists the recommended ceramic capacitors list for both 4.7- $\mu\text{H}$  and 10- $\mu\text{H}$  boost inductors.

If more cost-effective design is needed, use a 100- $\mu\text{F}$  electrolytic (low ESR) and a 10- $\mu\text{F}$  or 35-V ceramic capacitor.

**表 7-1. Boost Inductor and Capacitor Selections**

BOOST INDUCTOR	CAPACITORS	TOLERANCE (%)	RATING (V)	SIZE
10 $\mu\text{H}$	2 $\times$ 22 $\mu\text{F}$	$\pm 10$	35	1206
	2 $\times$ 10 $\mu\text{F}$	$\pm 10$	35	1206
4.7 $\mu\text{H}$	2 $\times$ 22 $\mu\text{F}$	$\pm 10$	35	1206
	2 $\times$ 10 $\mu\text{F}$	$\pm 10$	35	1206
	22 $\mu\text{F}$	$\pm 10$	35	1206

Figure 7-6 and Figure 7-7 show a bode plot of boost loop with 4.7- $\mu\text{H}$  and 10- $\mu\text{H}$  inductance and 4  $\mu\text{F}$ , 5  $\mu\text{F}$ , 7.5  $\mu\text{F}$ , 10  $\mu\text{F}$ , 15  $\mu\text{F}$ , and 20  $\mu\text{F}$  of boost capacitance after degrading. As the boost capacitance increases, the phase margin increases.

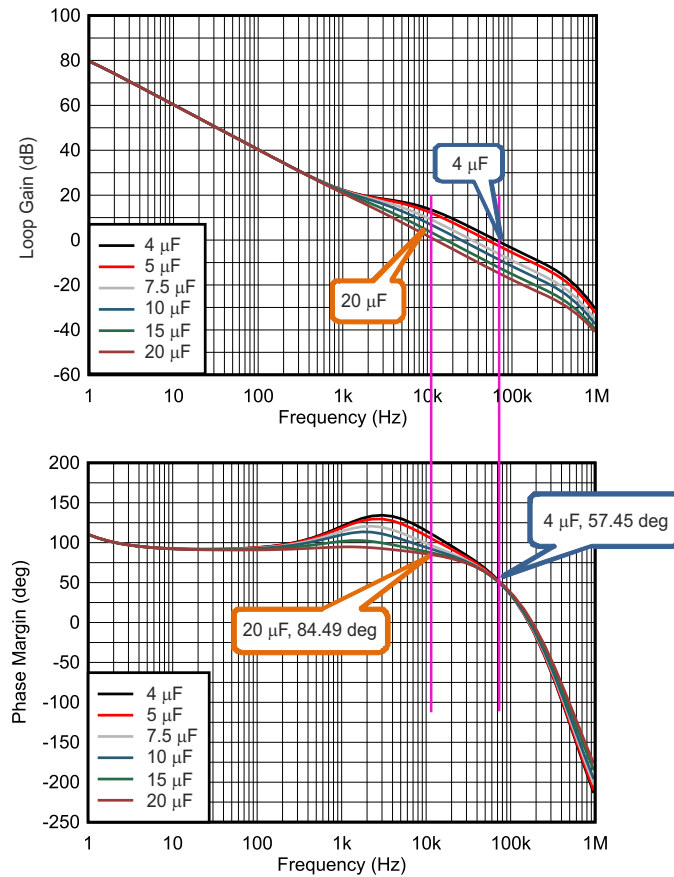


Figure 7-6. Gain and Phase Margin of the Boost Loop With Different Boost Capacitance ( $V_{\text{IN}} = 12 \text{ V}$ ,  $V_{\text{OUT}} = 18.2 \text{ V}$ ,  $I_{\text{LOAD}} = 1 \text{ A}$ ,  $f_{\text{SW}} = 1 \text{ MHz}$ , 4.7  $\mu\text{H}$ , Typical Bode Plot)

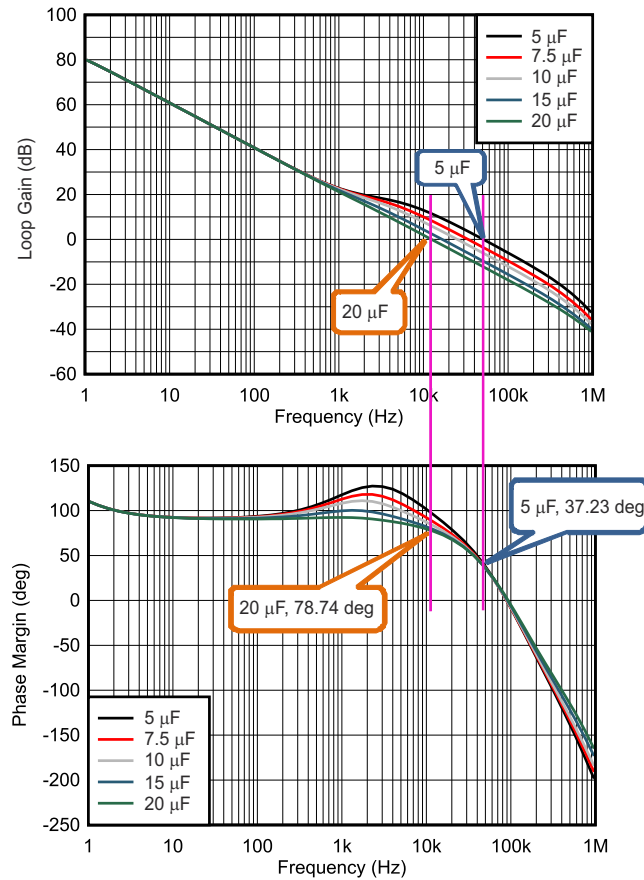


图 7-7. Gain and Phase Margin of the Boost Loop With Different Boost Capacitance ( $V_{IN} = 12\text{ V}$ ,  $V_{OUT} = 18.2\text{ V}$ ,  $I_{LOAD} = 1\text{ A}$ ,  $f_{SW} = 1\text{ MHz}$ ,  $10\text{ }\mu\text{H}$ , Typical Bode Plot)



### 7.3.11.3 Surge Components

If a surge test is required for the application, the D0 and D2 diodes should be added as the external protection components. If no surge test is required, remove the D0 and D2 diodes. 表 7-2 lists the recommended surge components.

表 7-2. Surge Components

DESIGNATOR	DESCRIPTION	PART NUMBER	MANUFACTURER <sup>(1)</sup>
D0	Diode, TVS, Uni, 28 V, 1500 W, SMC	SMCJ28A	Fairchild Semiconductor
D2	Diode, Schottky, 40 V, 2 A, SMA	B240A-13-F	Diodes Inc.

(1) See [Third-party Products Disclaimer](#)

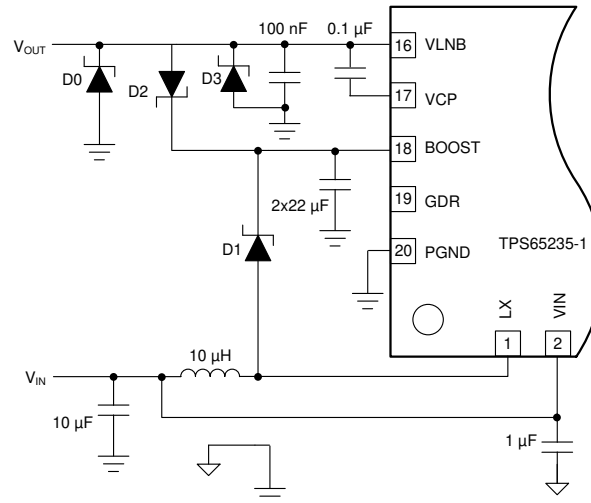


图 7-8. Surge Components Selection

### 7.3.11.4 Consideration for Boost Filtering and LNB Noise

Smaller capacitance on the BOOST pin reduces the cost of the system. However, when the inductor in system is the same, the smaller capacitance on the boost and the larger ripple on the LNB output.

## 7.4 Device Functional Modes

表 7-3 is the logic table for the device.

表 7-3. Logic table

EN	I2C_CON <sup>(1) (2) (3)</sup>	SCL	VCTRL	VLNB <sup>(4)</sup>
H	0	H	H	19.4 V
H	0	H	L	14.6 V
H	0	L	H	18.2 V
H	0	L	L	13.4 V
X	1	X	X	Controlled by VSET[3:0] bits at 0x01 register <sup>(5)</sup>
L	0	X	X	0 V

- (1) I2C\_CON is the bit7 of the I<sup>2</sup>C control register 0x01, which is used to set the VLNB output controlled by the I<sup>2</sup>C register or not.
- (2) When I<sup>2</sup>C interface is used in design, all the I<sup>2</sup>C registers are accessible even if the I2C\_CON bit is 0b.
- (3) When I2C\_CON is 1b, the VLNB output is controlled by the I<sup>2</sup>C control register even if the EN pin is low.
- (4) When I<sup>2</sup>C interface is used in design, it is recommended to set the I2C\_CON with 1b, if not, the LNB output will be variable because the SCL is toggled by the I<sup>2</sup>C register access as the clock signal.
- (5) Bit EN of the control register2 is used to disable or enable the LNB output, by default , the bit EN is 1b which enable the LNB output

## 7.5 Programming

### 7.5.1 Serial Interface Description

I<sup>2</sup>C is a 2-wire serial interface developed by Philips Semiconductor (see I<sup>2</sup>C-Bus Specification, Version 2.1, January 2000). The bus consists of a data line (SDA) and a clock line (SCL) with pullup structures. When the bus is idle, both SDA and SCL lines are pulled high external. All the I<sup>2</sup>C compatible devices connect to the I<sup>2</sup>C bus through open drain I/O pins, SDA and SCL. A master device, usually a microcontroller (MCU) or a digital signal processor (DSP), controls the bus. The master device is responsible for generating the SCL signal and device addresses. The master device also generates specific conditions that indicate the START and STOP of data transfer. A slave device receives, transmits data, or both on the bus under control of the master device.

The TPS65235-1 device works as a slave and supports the following data transfer modes, as defined in the I<sup>2</sup>C Bus Specification: standard mode (100 kbps), and fast mode (400 kbps). The interface adds flexibility to the power supply solution, enabling most functions to be programmed to new values depending on the instantaneous application requirements. Register contents remain intact as long as supply voltage remains above 4.5 V (typical).

The data transfer protocol for standard and fast modes is exactly the same; therefore, they are referred to as F/S-mode in this document. The TPS65235-1 device supports 7-bit addressing; 10-bit addressing and general call address are not supported.

The TPS65235-1 device has a 7-bit address set by ADDR pin. 表 7-4 shows how to set the I<sup>2</sup>C address.

表 7-4. I<sup>2</sup>C Address Selection

ADDR PIN	I <sup>2</sup> C ADDRESS	ADDRESS FORMAT (A6 ≥ A0)
Connect to VCC	0x08	000 1000b
Floating	0x09	000 1001b
Connected to GND	0x10	001 0000b
Resistor divider to make ADDR pin voltage in 3 V ~ V <sub>CC</sub> - 0.8 V	0x11	001 0001b

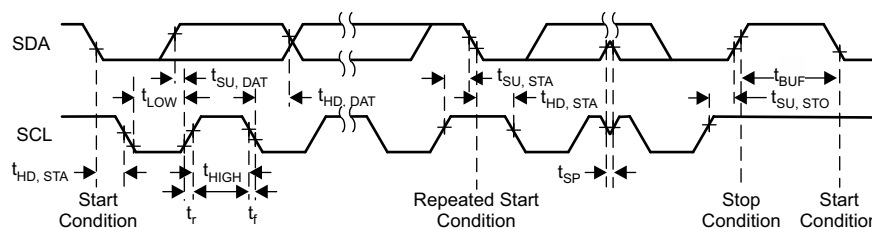


图 7-9. I<sup>2</sup>C Interface Timing Diagram

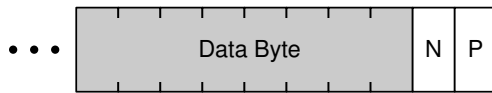
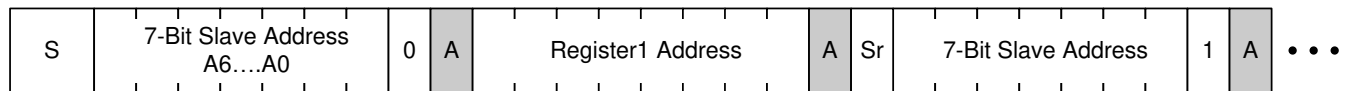
### 7.5.2 TPS65235-1 I<sup>2</sup>C Update Sequence

The TPS65235-1 requires a start condition, a valid I<sup>2</sup>C address, a register address byte, and a data byte for a single update. After the receipt of each byte, TPS65235-1 device acknowledges by pulling the SDA line low during the high period of a single clock pulse. TPS65235-1 performs an update on the falling edge of the LSB byte.

When the TPS65235-1 is disabled (EN pin tied to ground) the device cannot be updated via the I<sup>2</sup>C interface.



图 7-10. I<sup>2</sup>C Write Data Format



A: Acknowledge

N: Not Acknowledge

S: Start

P: Stop

Sr: Repeated Start

System Host

Chip

图 7-11. I<sup>2</sup>C Read Data Format

## 7.6 Register Maps

### 7.6.1 Control Register 1 (address = 0x00) [reset = 0x08]

**图 7-12. Control Register 1**

7		6		5		4		3		2		1		0	
I2C_CON		PWM/PSM		RESERVED				VSET[3:0]						EXTM TONE	
R/W-0b		R/W-0b		R/W-0b				R/W-0100b						R/W-0b	

**表 7-5. Control Register 1**

Bit	Field	Type	Reset	Description
7	I2C_CON	R/W	0b	0b = I <sup>2</sup> C control disabled 1b = I <sup>2</sup> C control enabled
6	PWM/PSM	R/W	0b	0b = PSM at light load 1b = Forced PWM
5	RESERVED	R/W	0b	Reserved
4-1	VSET[3:0]	R/W	0100b	LNB output voltage selection 0000b = 11 V 0001b = 11.6 V 0010b = 12.2 V 0011b = 12.8 V 0100b = 13.4 V 0101b = 14 V 0110b = 14.6 V 0111b = 15.2 V 1000b = 15.8 V 1001b = 16.4 V 1010b = 17 V 1011b = 17.6 V 1100b = 18.2 V 1101b = 18.8 V 1110b = 19.4 V 1111b = 20 V
0	EXTM TONE	R/W	0b	0b = EXTM 44-kHz tone input not support, with only 22-kHz tone output at VLNB 1b = EXTM 44-kHz tone input support, with 44-kHz tone output at VLNB

## 7.6.2 Control Register 2 (address = 0x01) [reset = 0x09]

图 7-13. Control Register 2

7	6	5	4	3	2	1	0
TONEAMP	TIMER	I <sub>sw</sub>	FSET	EN	DOUTMODE	TONE_AUTO	TONE_TRANS
R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-1b	R/W-0b	R/W-0b	R/W-1b

表 7-6. Control Register 2

Bit	Field	Type	Reset	Description
7	TONEAMP	R/W	0b	0b = 22-kHz tone amplitude is 650 mV (typ) 1b = 22-kHz tone amplitude is 750 mV (typ)
6	TIMER	R/W	0b	0b = Hiccup ON time set to 4 ms and OFF time set to 128 ms 1b = Hiccup ON time set to 8 ms and OFF time set to 256 ms
5	I <sub>sw</sub>	R/W	0b	0b = Boost switch peak current limit set to $3 \times I_{OCP} + 0.8$ A 1b = Boost switch peak current limit set to $5 \times I_{OCP} + 0.8$ A
4	FSET	R/W	0b	0b = 1-MHz switching frequency 1b = 500-kHz switching frequency
3	EN	R/W	1b	0b = LNB output disabled 1b = LNB output voltage Enabled
2	DOUTMODE	R/W	0b	0b = DOUT is kept to low when DIN has the tone input 1b = Reserved, cannot set to 1b
1	TONE_AUTO	R/W	0b	0b = GDR (External bypass FET control) is controlled by TONE_TRANS 1b = GDR (External bypass FET control) is automatically controlled by 22-kHz tones transmit
0	TONE_TRANS	R/W	1b	0b = GDR output with VLNB voltage for tone receive. Bypass FET is OFF for tone receiving from satellite 1b = GDR output with VCP voltage. Bypass FET is ON for tone transmit from TPS65235-1

表 7-7. 22-kHz Tone Receive Mode Selection

TONE_AUTO	TONE_TRANS	BYPASS FET
0b	0b	OFF
0b	1b	ON
1b	x	Auto Detect

The TPS65235-1 has full range of diagnostic flags for operation and debug. Processor can read the status register to check the error conditions. Once the error happens, the flags are changed, once the errors are gone, the flags are set back without I<sup>2</sup>C access.

If the TSD and OCP flags are triggered, FAULT pin will be pulled low, so FAULT pin can be the interrupt signal to processor. Once TSD and OCP are set to 1b, the FAULT pin logic is latched to low, processor need to read this status register to release the fault conditions.

### 7.6.3 Status Register (address = 0x02) [reset = 0x29]

**图 7-14. Status Register**

7	6	5	4	3	2	1	0
Reserved	0	LDO_ON	T125	TSD	OCP	CABLE_GOOD	VOUT_GOOD
R-0b	R-0b	R-0b	R-0b	R-1b	R-0b	R-0b	R-1b

**表 7-8. Status Register**

Bit	Field	Type	Reset	Description
7	Reserved	R	0b	Reserved
6	TDETGOOD	R	0b	0b = 22-kHz tone detected on DIN pin is out of range 1b = 22-kHz tone detected on DIN pin is in range
5	LDO_ON	R	1b	0b = Internal LDO is turned off but boost converter is on 1b = Internal LDO is turned on and boost converter is on
4	T125	R	0b	0b = Die temperature < 125°C 1b = Die temperature > 125°C
3	TSD	R	1b	0b = No thermal shutdown triggered 1b = Thermal shutdown triggered. The FAULT pin logic is latched to low, processor need to read this register to release the fault conditions
2	OCP	R	0b	0b = Overcurrent protection conditions released 1b = Overcurrent protection triggered. The FAULT pin logic is latched to low, processor need to read this register to release the fault conditions
1	CABLE_GOOD	R	0b	0b = Cable not connected 1b = Cable connection good
0	VOUT_GOOD	R	1b	0b = LNB output voltage out of range 1b = LNB output voltage in range

## 8 Application and Implementation

### 备注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The TPS65235 supports both DiSEqC1.x and DiSEqC2.x application. When the input voltage  $V_{IN}$  is greater than the expected output voltage  $V_{LNB}$ , the linear regulator drops the voltage difference between  $V_{IN}$  and  $V_{LNB}$ , which causes the lower efficiency and the higher power loss on the internal linear regulator if the current loading is high. For care must be taken to ensure that the safe operating temperature range of the TPS65235-1 is not exceeded. TI recommends operating the device in force PWM mode when  $V_{IN} > V_{OUT}$  to reduce output ripple.

### 8.2 Typical Application

#### 8.2.1 DiSEqC1.x Support

TPS65235-1 can operate in I<sup>2</sup>C and non-I<sup>2</sup>C interface mode. 图 8-1 shows the application with the device in I<sup>2</sup>C interface mode to support DiSEqC 1.x application. In non-I<sup>2</sup>C mode, the SCL, SDA, and ADDR pins can be floating.

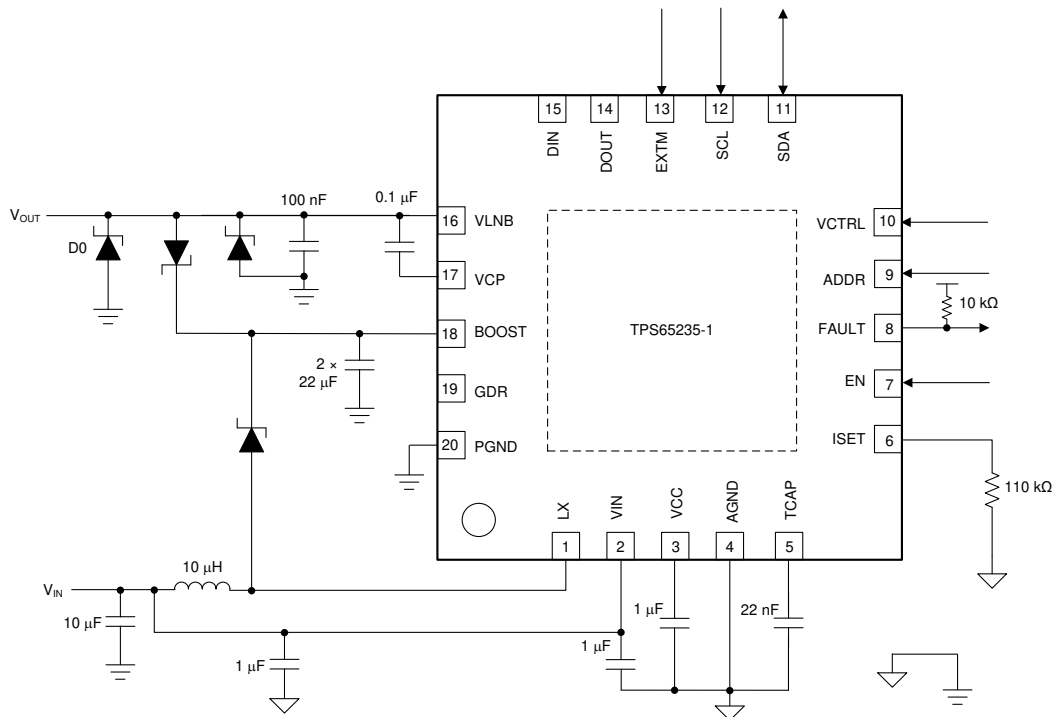


图 8-1. Application for DiSEqC1.x Support



### 8.2.1.1 Design Requirements

For this design example, use the parameters in [表 8-1](#).

**表 8-1. Design Parameters**

PARAMETER	VALUE
Input voltage range, $V_{IN}$	4.5 V to 20 V
Output voltage range $V_{LNB}$	11 V to 20 V
Output current range	0 A to 1 A

### 8.2.1.2 Detailed Design Procedure

To begin the design process, the following component values must be selected:

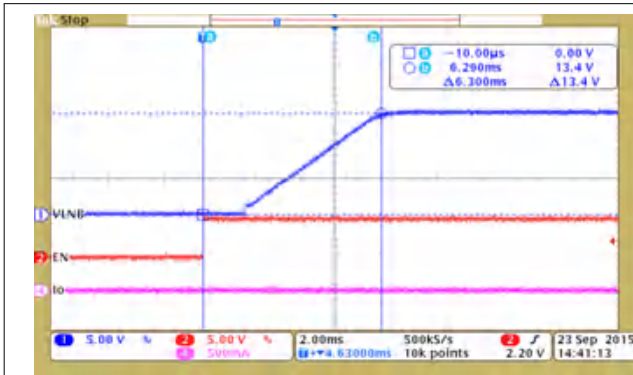
- Inductor
  - Choose the appropriate value of the inductor based on application cost requirements, ripple requirements, and [节 7.3.11](#).
- BOOST capacitor
  - Choose the appropriate BOOST capacitor value based on application cost requirements, ripple requirements, and [节 7.3.11](#).
- Diodes
  - The D0 and D2 diodes are used to help meet the surge-protection requirement of the application. If the application does not require surge protection, remove these diodes. For diode component selection, refer to [节 7.3.11.3](#).
  - The D1 diode is used for the boost loop. A Schottky diode is recommended for D1. The application requirements, which include input power range, output power range, and the current requirement, determine the current and voltage capability of the D1 diode.
  - The D3 diode is to help with the output protection for the VLNB voltage. A Schottky diode is recommended for D3. The application requirements determine the current and voltage capability of the D3 diode.

TPS65235-1

ZHCSG04E - JANUARY 2017 - REVISED MAY 2021

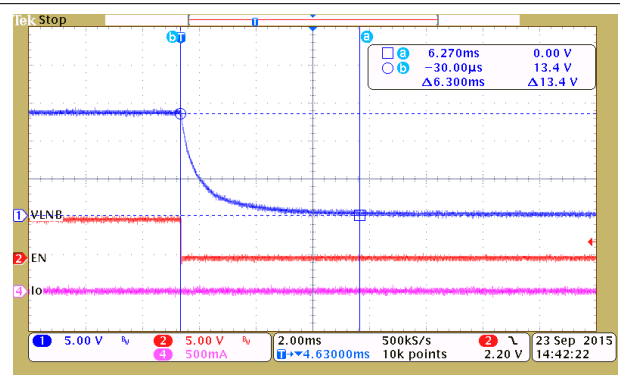
8.2.1.3 Application Curves

$T_A = 25^\circ\text{C}$ ,  $V_{IN} = 12\text{ V}$ ,  $f_{SW} = 1\text{ MHz}$ ,  $C_{Boost} = (2 \times 22\ \mu\text{F} / 35\text{ V})$  (unless otherwise noted)



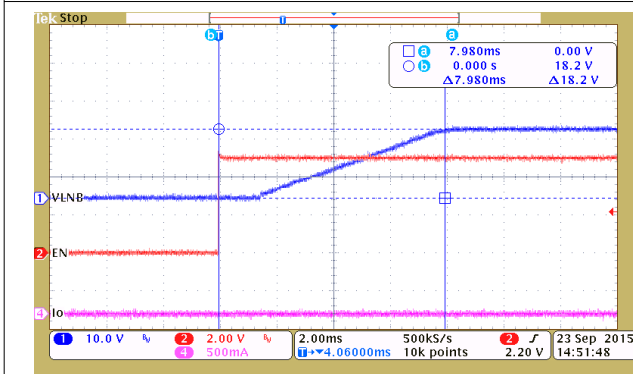
$V_{VLNB} = 13.4\text{ V}$

图 8-2. Soft Start, Delay from EN High to LNB Output High



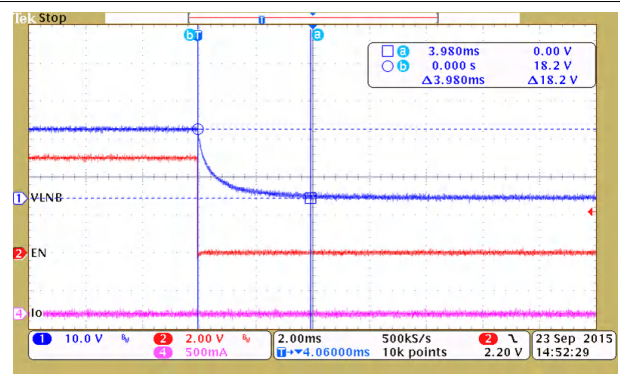
$V_{VLNB} = 13.4\text{ V}$

图 8-3. Disabled, Delay from EN Low to LNB Output Low



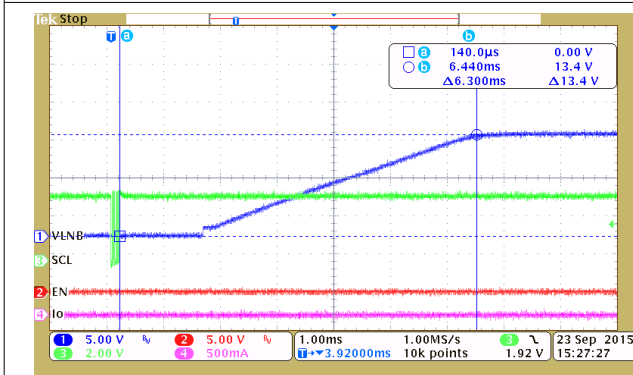
$V_{VLNB} = 18.2\text{ V}$

图 8-4. Soft-Start, Delay from EN High to LNB Output High



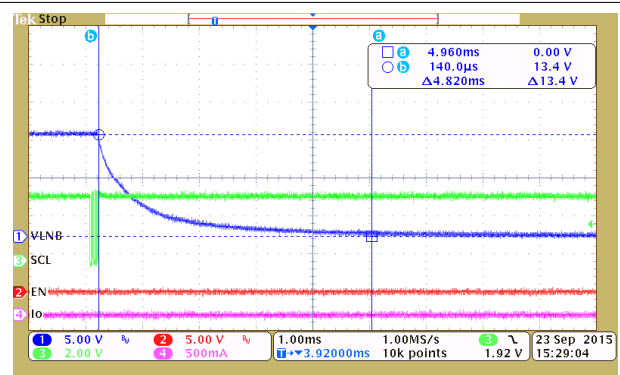
$V_{VLNB} = 18.2\text{ V}$

图 8-5. Disabled, Delay From EN Low to LNB Output Low



EN = 0b  $V_{VLNB} = 13.4\text{ V}$

图 8-6. Soft Start, Delay From I<sup>2</sup>C Enable (I<sup>2</sup>C\_CON = 1b) to LNB Output High



EN = 0b  $V_{VLNB} = 13.4\text{ V}$

图 8-7. Delay From I<sup>2</sup>C Disable (I<sup>2</sup>C\_CON = 0b) to LNB Output Low

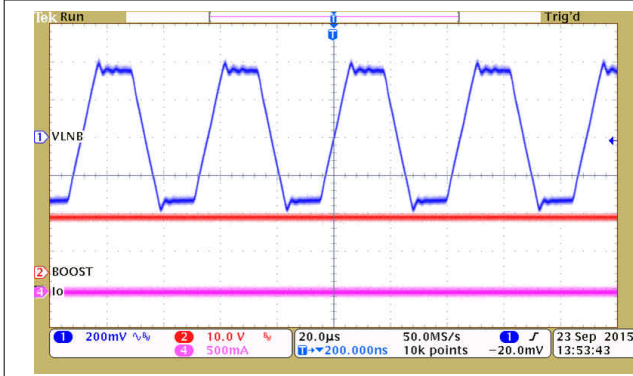


图 8-8. No Load, 22-kHz Tone Output

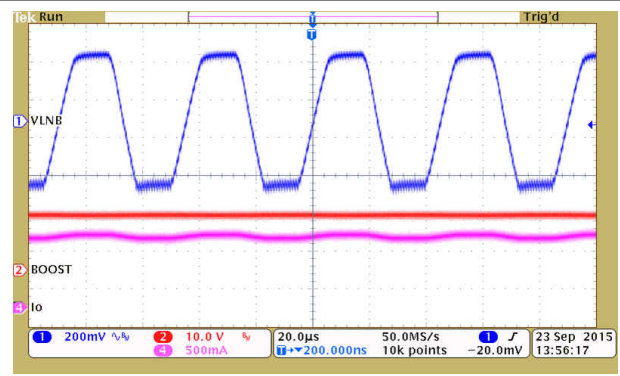


图 8-9. 950-mA Load, 22-kHz Tone Output

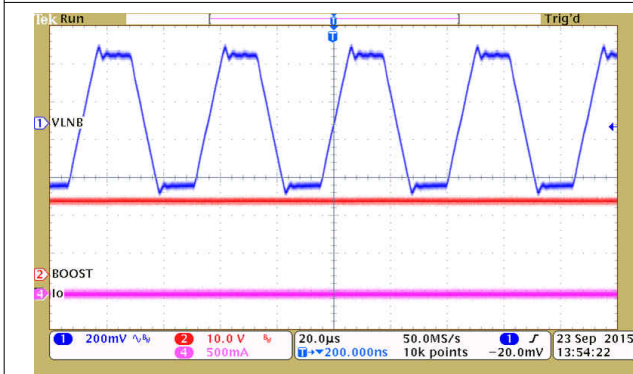


图 8-10. No Load, 22-kHz Tone Output

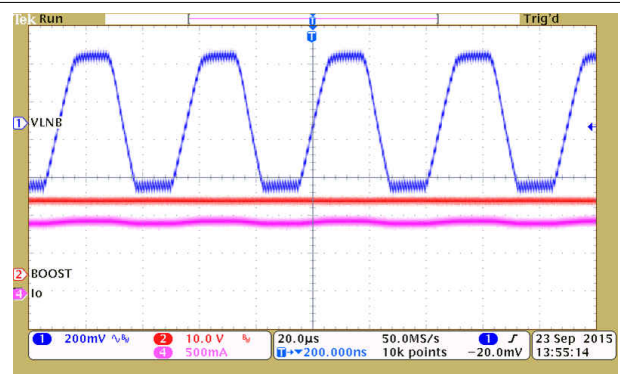


图 8-11. 950-mA Load, 22-kHz Tone Output

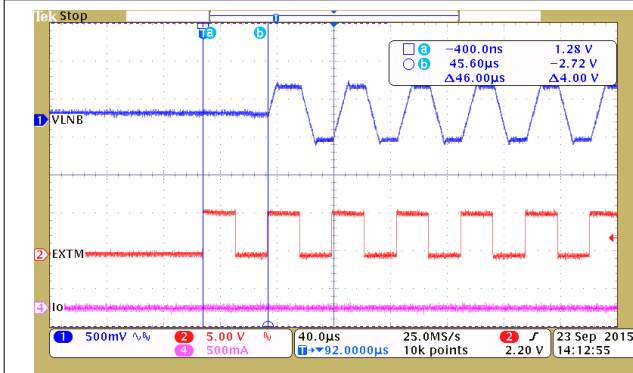


图 8-12. No load, 22-kHz Tone Delay from EXTM 22-kHz Input Turns High to Output Tone On

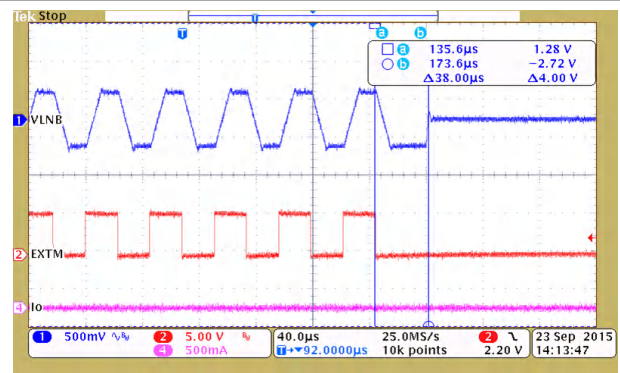


图 8-13. No load, 22-kHz Tone Delay from EXTM 22-kHz Input Turns Low to Output Tone Off

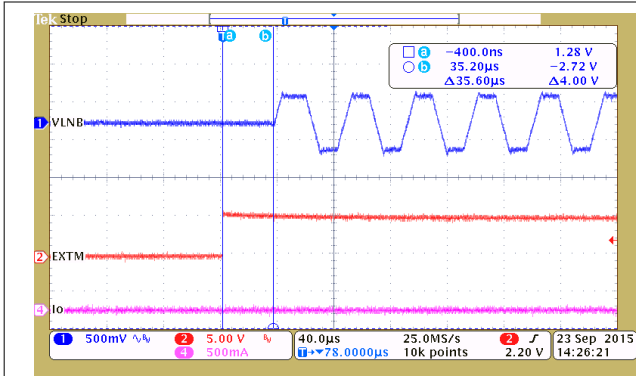


图 8-14. No Load, 22-kHz Tone Delay from EXTM Tone Envelop Input Turns High to Output Tone On

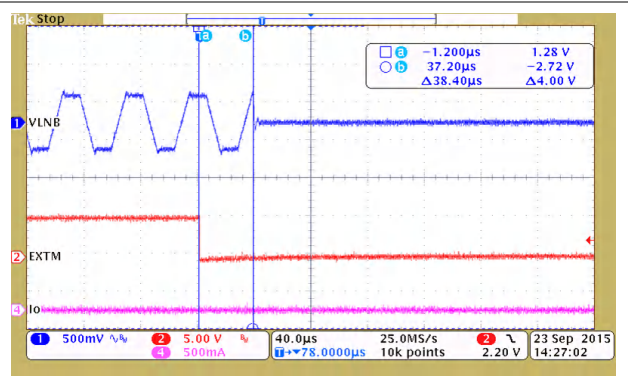


图 8-15. No Load, 22-kHz Tone Delay from EXTM Tone Envelop Input Turns Low to Output Tone Off

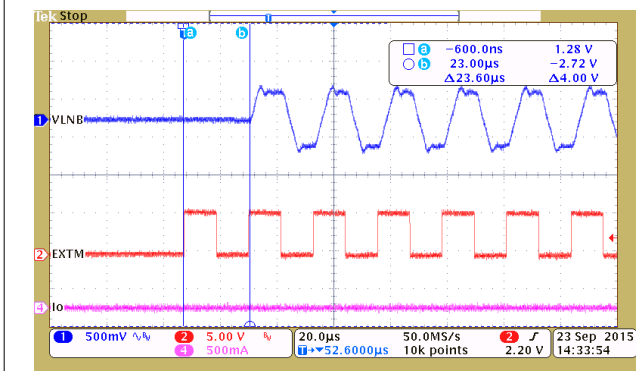


图 8-16. No Load, 44-kHz Tone Delay from EXTM 22-kHz Input Turns High to Output Tone On

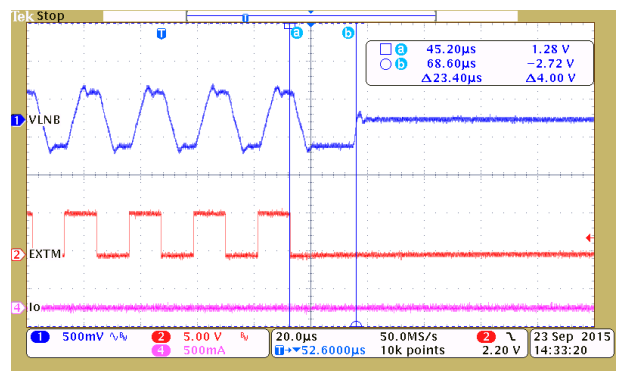


图 8-17. No Load, 44-kHz Tone Delay from EXTM 22-kHz Input Turns Low to Output Tone Off

## 8.2.2 DiSEqC2.x Support

The TPS65235-1 can support both DiSEqC 1.x application and DiSEqC 2.x application. 图 8-18 shows the application for supporting DiSEqC 2.x application.

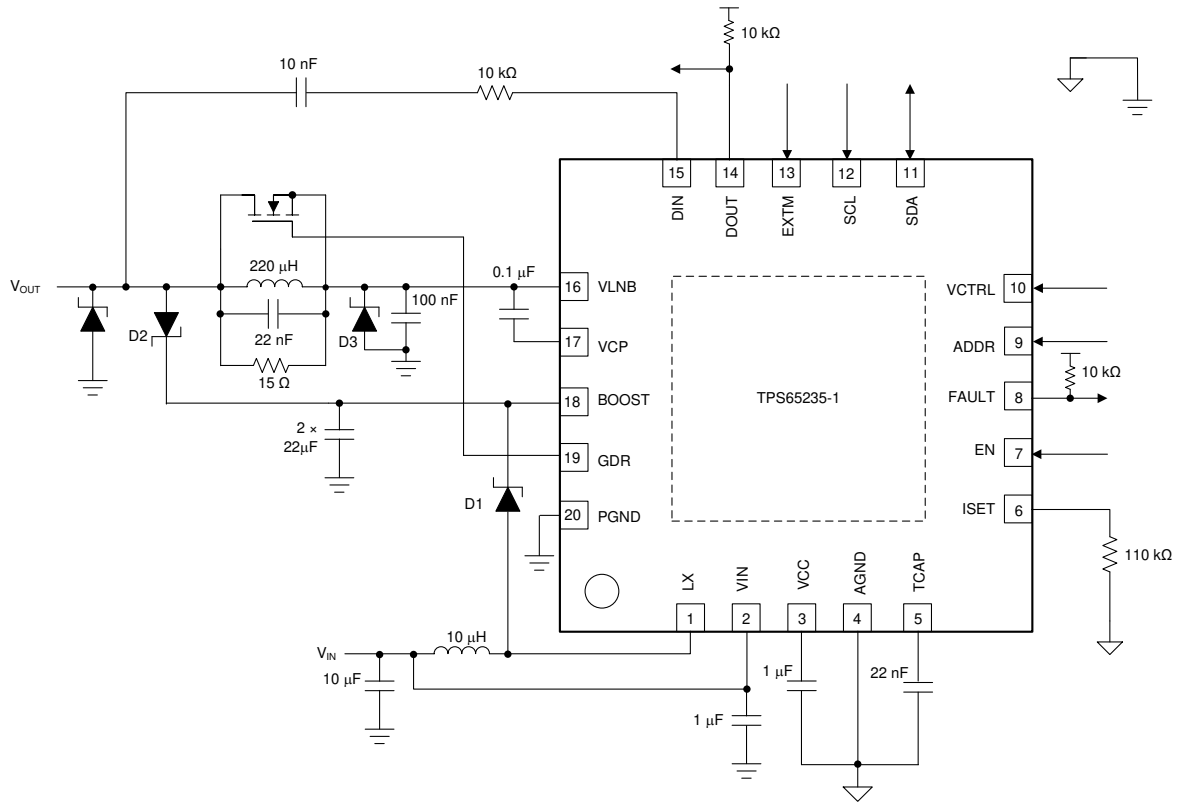


图 8-18. Application Schematic for DiSEqC2.x Support

### 8.2.2.1 Design Requirements

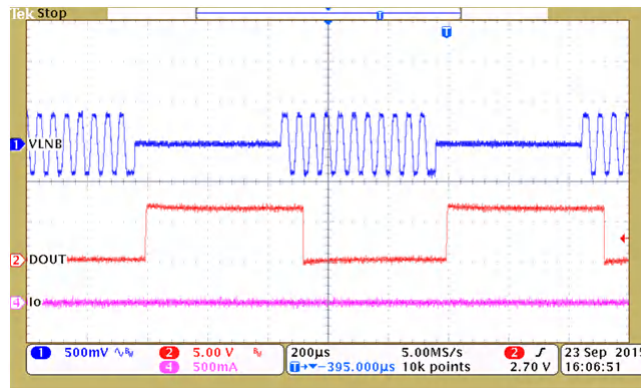
Refer to the 节 8.2.1 section for design requirements.

### 8.2.2.2 Detailed Design Procedure

Refer to the 节 8.2.1 section for detailed design procedures.

### 8.2.2.3 Application Curve

Refer to the [§ 8.2.1](#) section for typical application curves. [图 8-19](#) is the unique tone-detection curve for the DiSEqC 2.x application.



**图 8-19. DOUT Tone Detection Output**

## 9 Power Supply Recommendations

The device is designed to operate from an input supply ranging from 4.5 V to 20 V. The input supply should be well regulated. If the input supply is located more than a few inches from the converter, an additional bulk capacitance, typically with a value 100  $\mu$ F, may be required in addition to the ceramic bypass capacitors.

## 10 Layout

### 10.1 Layout Guidelines

The TPS65235-1 is designed to layout in 2 - layer PCB. To ensure reliability of the device, following common printed-circuit board layout guidelines is recommended.

- It is critical to make sure the ground of input capacitor, output capacitor, and the boost converter are connected at one point at same layer.
- The PGND and AGND pins are located in different regions. Connect these grounds to the thermal pad. Other components are connected the AGND pin.
- Put the BOOST capacitors as close as possible.
- The loop from the VIN inductor to the LX pin should be as short as possible.
- The loop from the VIN inductor to D1 Schottky diode to the BOOST should be as short as possible.
- The loop for boost capacitors to the PGND pin should be within the loop from the LX pin to D1 Schottky diode to the BOOST pin.

## 10.2 Layout Example

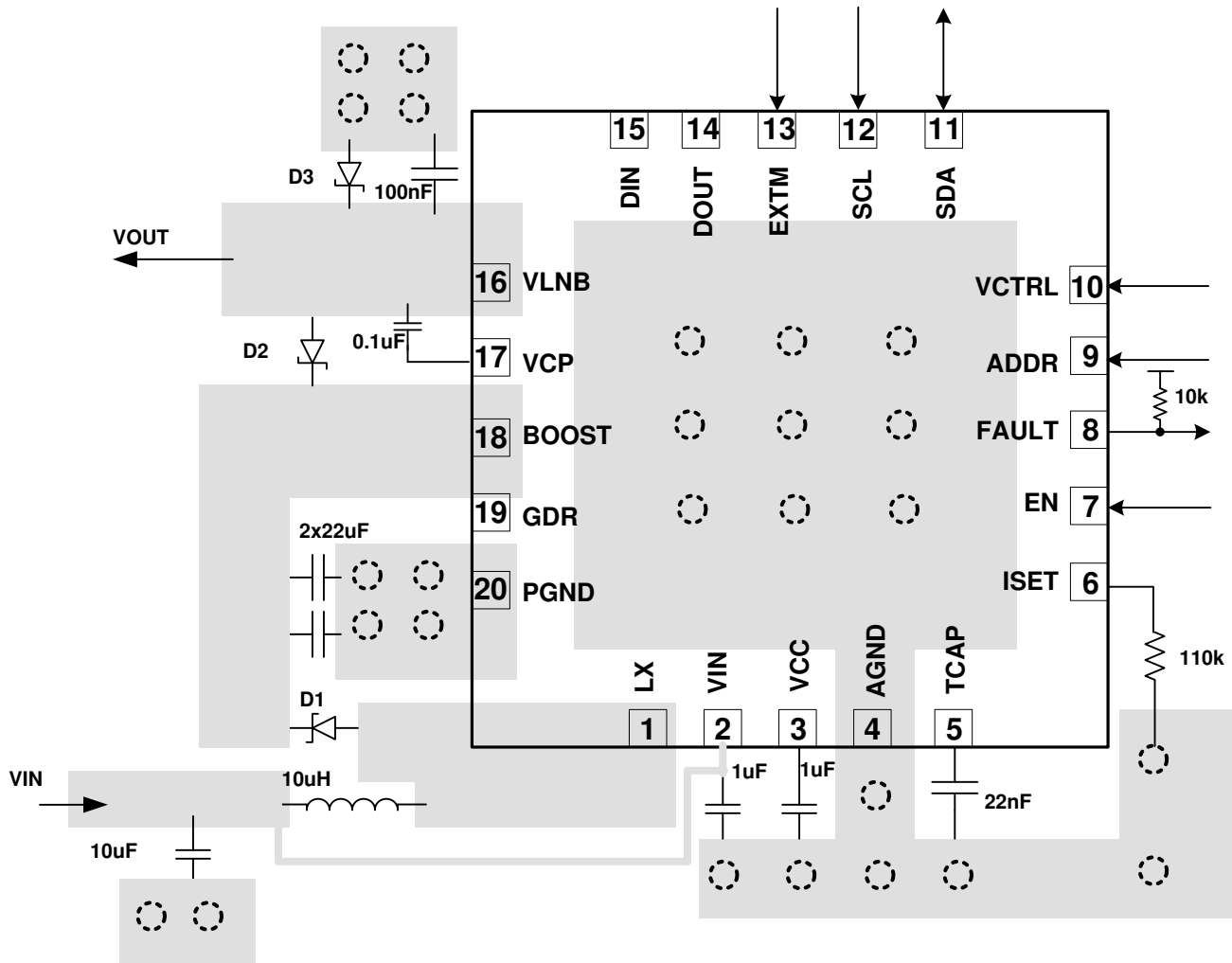


图 10-1. Layout



## 11 Device and Documentation Support

### 11.1 Device Support

### 11.2 Documentation Support

#### 11.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [Evaluation Module for the TPS65235-1 LNB Voltage Regulator With I<sup>2</sup>C Interface for DiSEqC2.x Application user's guide](#)
- Texas Instruments, [Evaluation Module for the TPS65235-1 LNB Voltage Regulator With I<sup>2</sup>C Interface for DiSEqC1.x Application user's guide](#)

### 11.3 接收文档更新通知

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### 11.4 支持资源

[TI E2E™ 支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

### 11.5 Trademarks

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### 11.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 11.7 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS65235-1RUKR	ACTIVE	WQFN	RUK	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	652351	<a href="#">Samples</a>
TPS65235-1RUKT	ACTIVE	WQFN	RUK	20	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	652351	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBsolete:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**

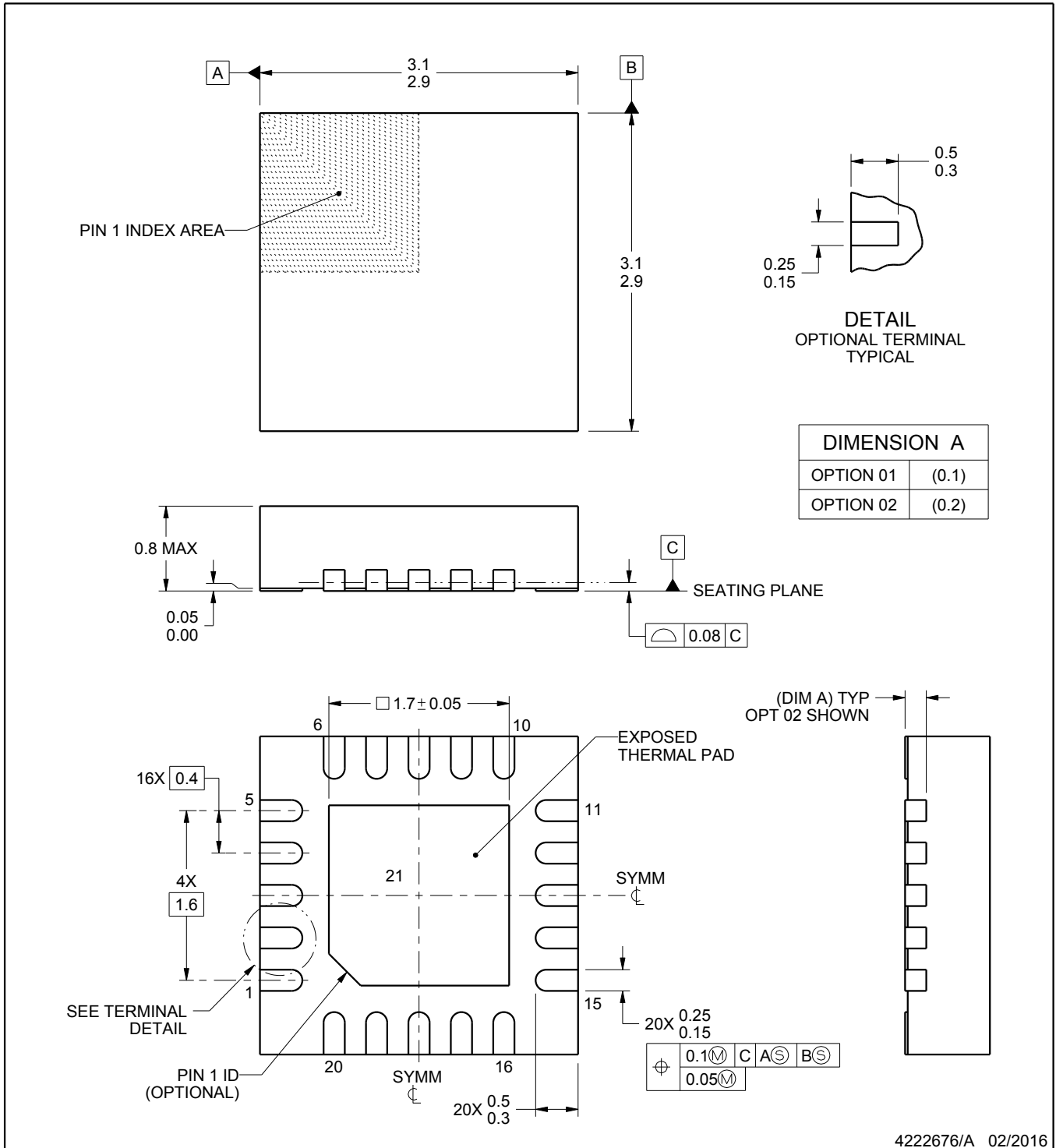
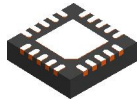

\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS65235-1RUKR	WQFN	RUK	20	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TPS65235-1RUKT	WQFN	RUK	20	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS65235-1RUKR	WQFN	RUK	20	3000	367.0	367.0	35.0
TPS65235-1RUKT	WQFN	RUK	20	250	210.0	185.0	35.0



4222676/A 02/2016

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

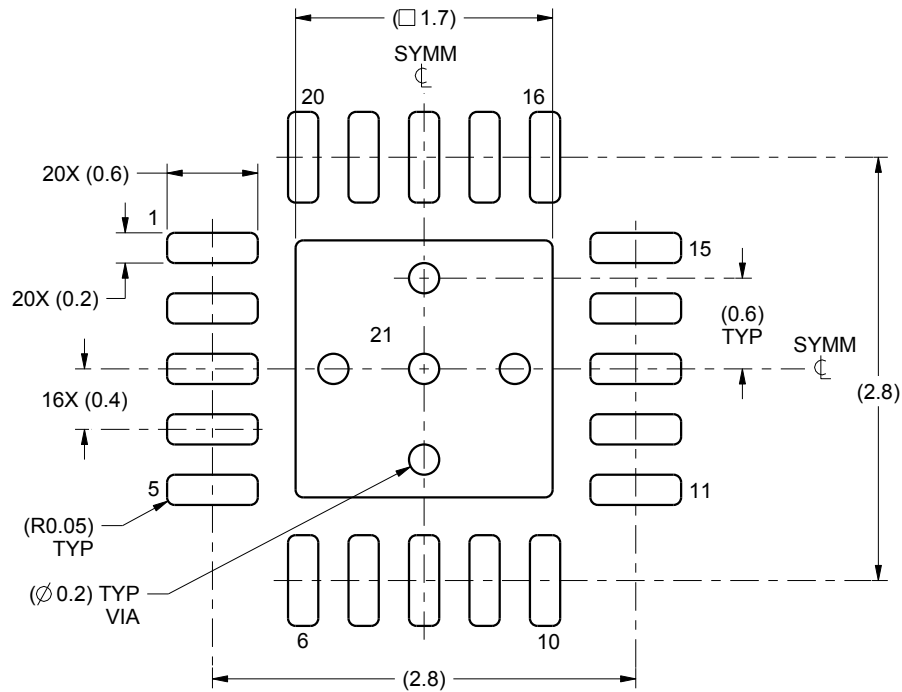


# EXAMPLE BOARD LAYOUT

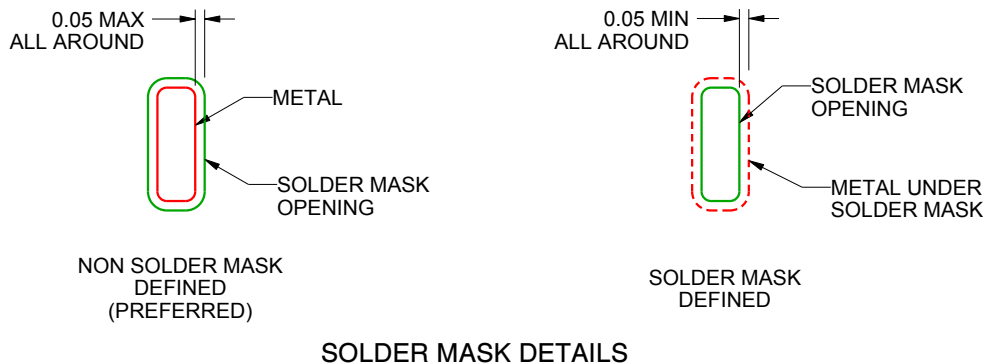
RUK0020B

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE  
SCALE:20X



SOLDER MASK DETAILS

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NOTES: (continued)

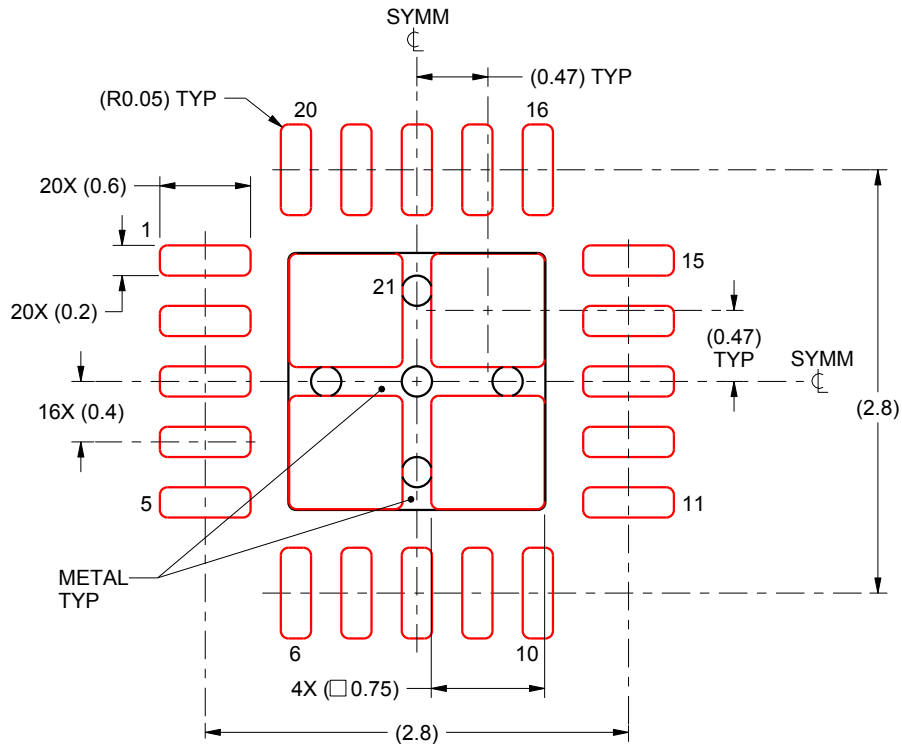
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

RUK0020B

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



## SOLDER PASTE EXAMPLE BASED ON 0.1 mm THICK STENCIL

EXPOSED PAD 21:  
78% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE  
SCALE:20X

4222676/A 02/2016

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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